适用于汽车应用的 LM2904-Q1、LM2904B-Q1 业界通用双路运算放大器

1 特性

- 符合面向汽车应用的 AEC Q-100 标准
  - 温度等级 1：-40°C 至 +125°C
  - 器件 HBM ESD 分类等级 2
  - 器件 CDM ESD 分类等级 C5
- 宽电源电压范围为 3V 至 36V (LM2904B-Q1)
- 每通道电源电流 300µA（LM2904B-Q1，典型值）
- 单位增益带宽为 1.2MHz (LM2904B-Q1)
- 共模输入电压范围包括接地，支持近地直接检测
- 低输入失调电压在 25°C 时为 3mV（LM2904B-Q1，最大值）
- 内部射频和 EMI 滤波器 (LM2904B-Q1)

2 应用

- 汽车照明
- 车身电子装置
- 汽车音响主机
- 远程信息处理控制单元
- 紧急呼叫 (eCall)
- 被动安全：制动系统
- 电动汽车/混合动力电动汽车：
  - 逆变器和电机控制
  - 车载充电器 (OBC) 和无线充电器
  - 电池管理系统 (BMS)

3 说明

LM2904-Q1 和 LM2904B-Q1 是符合 AEC-Q100 规范的工业标准运算放大器，适合汽车使用。LM2904B-Q1 是 LM2904-Q1 的下一代版本，包含两个高电压 (36V) 运算放大器。LM2904B-Q1 为成本敏感性 应用带来了出色的价值，该器件的 特性 包括低失调电压（1mV，典型值）、接地共模输入范围以及高差分输入电压能力。

LM2904B-Q1 利用单位增益稳定性、更低的失调电压（1mV，典型值）和更低的静态电流（300µA，典型值）等增强型 特性 简化电路设计。高 ESD（2kV，HBM）和集成 EMI 和射频滤波器可支持将 LM2904B-Q1 器件用于 汽车市场 中最严苛、最具环境挑战性的应用。

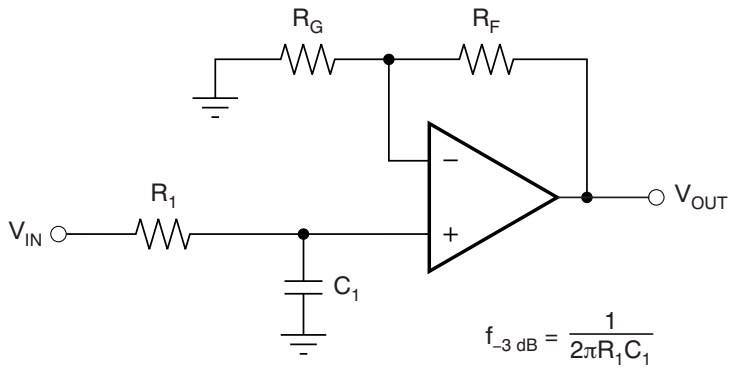
器件信息(1)

器件型号	封装	封装尺寸（标称值）
LM2904B-Q1	SOIC (8)	4.90mm × 3.90mm
	TSSOP (8)(2)	3.00mm × 4.40mm
	SOT23- (8)(2) 中添加了 SOT23-8 封装信息	1.60mm × 2.90mm
LM2904-Q1	SOIC (8)	4.90mm × 3.90mm
	TSSOP (8)	3.00mm × 4.40mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

(2) 此封装仅为预览版。

单极低通滤波器



$$f_{-3\,dB} = \frac{1}{2\pi R_1 C_1}$$

$$\frac{V_{OUT}}{V_{IN}} = \left(1 + \frac{R_F}{R_G}\right)\left(\frac{1}{1 + sR_1C_1}\right)$$

目录

4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

Changes from Revision G (February 2019) to Revision H **Page**

- 已添加 向器件信息表 ... 1
- Added information on SOT23-8 package to the *Device Comparison Table* ... 3
- 已添加 the *Typical Characteristics* section for the LM2904B-Q1 device ... 9
- 已添加 test circuit for THD+N and small-signal step response, G = –1 in the *Parameter Measurement Information* section ... 16
- Changed specific voltages to a *Recommended Operating Conditions* reference ... 17
- 已更改 the functional block diagram for LM2904B-Q1 in the *Detailed Description* section ... 17

Changes from Revision F (April 2008) to Revision G **Page**

- 已添加 *应用* 部分、*ESD 额定值* 表、*特性* *说明* 部分、*器件功能模式*、*应用和实施* 部分、*电源建议* 部分、*布局* 部分、*器件和文档支持* 部分以及*机械、封装和可订购信息* 部分 ... 1
- 已添加 向数据表添加了新器件 ... 1
- 已添加 AEC-Q100 认证声明 ... 1

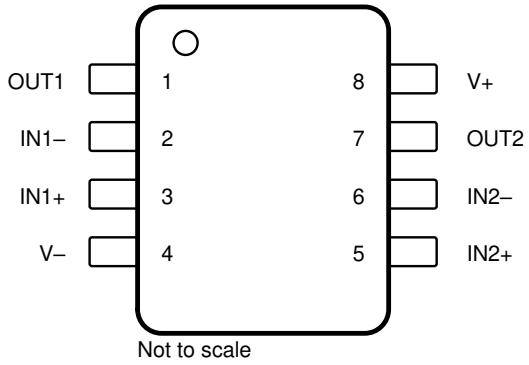
5 Device Comparison Table

PART NUMBER	SUPPLY VOLTAGE	AMBIENT TEMPERATURE RANGE	V_{OS} (MAXIMUM AT 25°C)	I_Q / CH (TYPICAL AT 25°C)	INTEGRATED EMI FILTER	PACKAGE
LM2904B-Q1	3 V to 36 V	–40°C to 125°C	3 mV	300 µA	Yes	D, DDF(1), PW(1)
LM2904-Q1	3 V to 26 V	–40°C to 125°C	7 mV	350 µA	No	D, PW
LM2904V-Q1	3 V to 32 V	–40°C to 125°C	7 mV	350 µA	No	D, PW
LM2904AV-Q1	3 V to 32 V	–40°C to 125°C	2 mV	350 µA	No	D, PW

(1) Packages for this device are preview only.

6 Pin Configuration and Functions

D, DDF(1), and PW(1) Packages
8-Pin SOIC, SOT23-8, and TSSOP
Top View



Not to scale

(1) Package is preview only.

Pin Functions

PIN		I/O	DESCRIPTION
NAME	SOIC, SOT23-8, and TSSOP(1)		
IN1–	2	I	Negative input
IN1+	3	I	Positive input
IN2–	6	I	Negative input
IN2+	5	I	Positive input
OUT1	1	O	Output
OUT2	7	O	Output
V–	4	—	Negative (lowest) supply or ground (for single-supply operation)
V+	8	—	Positive (highest) supply

(1) For a listing of which devices are available in what packages, see the *Device Comparison Table* section.

7 Specifications

7.1 Absolute Maximum Ratings

over operating ambient temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
Supply voltage, V_S = ([V+] – [V–])		LM2904B-Q1		40	V
		LM2904V-Q1, LM2904AV-Q1		32	
		LM2904-Q1		26	
Differential input voltage, V_{ID}(2)		LM2904B-Q1, LM2904V-Q1, LM2904AV-Q1	–32	32	V
		LM2904-Q1	–26	26	
Input voltage, V_I	Either input	LM2904B-Q1	–0.3	40	V
		LM2904V-Q1, LM2904AV-Q1	–0.3	32	
		LM2904-Q1	–0.3	26	
Duration of output short circuit (one amplifier) to V– at (or below) T_A = 25°C, V_S ≤ 15 V(3)			Unlimited		s
Operating ambient temperature, T_A			–40	125	°C
Operating virtual-junction temperature, T_J				150	°C
Storage temperature, T_{stg}			–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) Differential voltages are at IN+, with respect to IN−.
(3) Short circuits from outputs to the supply pins can cause excessive heating and eventual destruction.

7.2 ESD Ratings

			VALUE	UNIT
LM2904B-Q1				
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per AEC Q100-002(1)	±2000	V
		Charged-device model (CDM), per AEC Q100-011	±750	
LM2904-Q1, LM2904AV-Q1, AND LM2904V-Q1				
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per AEC Q100-002(1)	±1000	V
		Charged-device model (CDM), per AEC Q100-011	±500	

(1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

7.3 Recommended Operating Conditions

over operating ambient temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_S	Supply voltage, V_S = ([V+] – [V–])	LM2904B-Q1	3	36	V
		LM2904AV-Q1, LM2904V-Q1	3	30	
		LM2904-Q1	3	26	
V_{CM}	Common-mode voltage		V–	(V+) – 2	V
T_A	Operating ambient temperature		–40	125	°C

7.4 Thermal Information

THERMAL METRIC[1]		LM2904-Q1, LM2904AV-Q1, LM2904B-Q1,LM2904V-Q1[2]		UNIT
		D (SOIC)	PW (TSSOP)	
		8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	124.7	171.7	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	66.9	68.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	67.9	99.2	°C/W
ψ_{JT}	Junction-to-top characterization parameter	19.2	11.5	°C/W
ψ_{JB}	Junction-to-board characterization parameter	67.2	97.9	°C/W

(1) For more information about traditional and new thermal metrics, see *Semiconductor and IC Package Thermal Metrics*.
(2) For a listing of which devices are available in what packages, see *Device Comparison Table*.

7.5 Electrical Characteristics: LM2904B-Q1

V_S = (V+) – (V–) = 5 V – 36 V (±2.5 V – ±18 V), T_A = 25°C, V_{CM} = V_{OUT} = V_S / 2, R_L = 10k connected to V_S / 2 (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
OFFSET VOLTAGE								
V_{OS}	Input offset voltage	LM2904B-Q1				±0.3	±3.0	mV
				T_A = –40°C to +125°C			±4	
dV_{OS}/d_T	Input offset voltage drift			T_A = –40°C to +125°C(1)		±3.5	12	µV/°C
PSRR	Power supply rejection ratio					±2	15	µV/V
	Channel separation, dc	f = 1 kHz to 20 kHz				±1		µV/V
INPUT VOLTAGE RANGE								
V_{CM}	Common-mode voltage range	V_S = 3 V to 36 V			(V–)		(V+) – 1.5	V
		V_S = 5 V to 36 V		T_A = –40°C to +125°C	(V–)		(V+) – 2	
CMRR	Common-mode rejection ratio	(V–) ≤ V_{CM} ≤ (V+) – 1.5 V	V_S = 3 V to 36 V			20	100	µV/V
		(V–) ≤ V_{CM} ≤ (V+) – 2.0 V	V_S = 5 V to 36 V	T_A = –40°C to +125°C		25	316	
INPUT BIAS CURRENT								
I_B	Input bias current					±10	±35	nA
				T_A = –40°C to +125°C(1)			±50	
I_{OS}	Input offset current					0.5	4	nA
				T_A = –40°C to +125°C(1)			5	
dI_{OS}/d_T	Input offset current drift			T_A = –40°C to +125°C		10		pA/°C
NOISE								
E_n	Input voltage noise	f = 0.1 to 10 Hz				3		$µV_{PP}$
e_n	Input voltage noise density	f = 1 kHz				40		nV/√Hz
INPUT IMPEDANCE								
Z_{ID}	Differential					10 || 0.1		MΩ || pF
Z_{IC}	Common-mode					4 || 1.5		GΩ || pF
OPEN-LOOP GAIN								
A_{OL}	Open-loop voltage gain	V_S = 15 V; V_O = 1 V to 11 V; R_L ≥ 10 kΩ, connected to (V–)			70	140		V/mV
				T_A = –40°C to +125°C	35			
FREQUENCY RESPONSE								
GBW	Gain bandwidth product					1.2		MHz
SR	Slew rate	G = +1				0.5		V/µs
$Θ_m$	Phase margin	G = +1, R_L = 10 kΩ, C_L = 20 pF				56		°
t_{OR}	Overload recovery time	V_{IN} × gain > V_S				10		µs
t_s	Settling time	To 0.1%, V_S = 5 V, 2-V step , G = +1, C_L = 100 pF				4		µs
THD+N	Total harmonic distortion + noise	G = +1, f = 1 kHz, V_O = 3.53 V_{RMS}, V_S = 36 V, R_L = 100k, I_{OUT} ≤ ±50 µA, BW = 80 kHz				0.001%		
OUTPUT								
V_O	Voltage output swing from rail	Positive rail (V+)		I_{OUT} = 50 µA		1.35	1.42	V
				I_{OUT} = 1 mA		1.4	1.48	
				I_{OUT} = 5 mA(1)		1.5	1.61	
		Negative rail (V–)		I_{OUT} = 50 µA		100	150	mV
				I_{OUT} = 1 mA		0.75	1	V
			V_S = 5 V, RL ≤ 10 kΩ connected to (V–)	T_A = –40°C to +125°C		5	20	mV
I_O	Output current	V_S = 15 V; V_O = V–; V_{ID} = 1 V	Source(1)		–20	–30		mA
				T_A = –40°C to +125°C	–10			
		V_S = 15 V; V_O = V+; V_{ID} = –1 V	Sink(1)		10	20		
				T_A = –40°C to +125°C	5			
		V_{ID} = –1 V; V_O = (V–) + 200 mV			60	100		µA
I_{SC}	Short-circuit current	V_S = 20 V, (V+) = 10 V, (V–) = –10 V, V_O = 0 V				±40	±60	mA
C_{LOAD}	Capacitive load drive					100		pF
R_O	Open-loop output resistance	f = 1 MHz, I_O = 0 A				300		Ω
POWER SUPPLY								
I_Q	Quiescent current per amplifier	V_S = 5 V; I_O = 0 A		T_A = –40°C to +125°C		300	460	µA
		V_S = 36 V; I_O = 0 A					800	

(1) Specified by characterization only.

7.6 Electrical Characteristics: LM2904-Q1, LM2904AV-Q1, LM2904V-Q1

For V_S = (V+) – (V–) = 5 V, T_A = 25°C, R_L = 10 kΩ connected to V– (unless otherwise noted)

PARAMETER		TEST CONDITIONS[1]			MIN	TYP	MAX	UNIT
OFFSET VOLTAGE								
V_{OS}	Input offset voltage	V_S = 5 V to maximum; V_{CM} = 0 V; V_O = 1.4 V	LM2904-Q1, LM2904V-A1			±3	±7	mV
				T_A = –40°C to 125°C			±10	
			LM2904AV-Q1			±1	±2	
				T_A = –40°C to 125°C			±4	
dV_{OS}/d_T	Input offset voltage drift			T_A = –40°C to 125°C		±7		µV/°C
PSRR	Input offset voltage vs power supply ($\Delta V_{IO}/\Delta V_S$)	V_S = 5 V to 30 V			65	100		dB
V_{O1}/V_{O2}	Channel separation	f = 1 kHz to 20 kHz				120		dB
INPUT VOLTAGE RANGE								
V_{CM}	Common-mode voltage range	V_S = 5 V to maximum			(V–)		(V+) – 1.5	V
				T_A = –40°C to 125°C	(V–)		(V+) – 2	
CMRR	Common-mode rejection ratio	V_S = 5 V to maximum; V_{CM} = 0 V			65	80		dB
INPUT BIAS CURRENT								
I_B	Input bias current	V_O = (V–) + 1.4 V				–20	–250	nA
				T_A = –40°C to 125°C			–500	
I_{OS}	Input offset current	V_O = (V–) + 1.4 V	LM2904-Q1			2	50	nA
				T_A = –40°C to 125°C			300	
			LM2904AV-Q1, LM2904V-Q1			2	50	
				T_A = –40°C to 125°C			150	
dI_{OS}/d_T	Input offset current drift			T_A = –40°C to 125°C		10		pA/°C
NOISE								
e_n	Input voltage noise density	f = 1 kHz				40		nV/√Hz
OPEN-LOOP GAIN								
A_{OL}	Open-loop voltage gain	V_S = 15 V; V_O = (V–) + 1 V to (V–) + 11 V; R_L ≥ 2 kΩ, connected to (V–)			25	100		V/mV
				T_A = –40°C to 125°C	15			
FREQUENCY RESPONSE								
GBW	Gain bandwidth product					0.7		MHz
SR	Slew rate	G = +1				0.3		V/µs
OUTPUT								
V_O	Voltage output swing from rail	Positive rail	R_L ≥ 10 kΩ		V_S – 1.5			V
			LM2904-Q1	V_S = maximum; R_L = 2 kΩ	4			
				V_S = maximum; R_L ≥ 10 kΩ	3	2		
			LM2904AV-Q1, LM2904V-Q1	V_S = maximum; R_L = 2 kΩ	6			
				V_S = maximum; R_L ≥ 10 kΩ	5	4		
		Negative rail		V_S = 5 V; R_L ≤ 10 kΩ		5	20	mV
I_O	Output current	V_S = 15 V; V_O = V–; V_{ID} = 1 V	Source		–20	–30		mA
				T_A = –40°C to 125°C	–10			
		V_S = 15 V; V_O = V+; V_{ID} = –1 V	Sink		10	20		
				T_A = –40°C to 125°C	5			
		V_{ID} = –1 V; V_O = (V–) + 200 mV	LM2904-Q1			30		µA
			LM2904AV-Q1, LM2904V-Q1		12	40		
I_{SC}	Short-circuit current	V_S = 10 V; V_O = V_S / 2				±40	±60	mA
POWER SUPPLY								
I_Q	Quiescent current per amplifier	V_O = V_S / 2; I_O = 0 A		T_A = –40°C to 125°C		350	600	µA
		V_S = maximum; V_O = maximum / 2; I_O = 0 A				500	1000	

(1) All characteristics are measured with zero common-mode input voltage, unless otherwise specified. Maximum V_S for testing purposes is 26 V for LM2904-Q1 and 32 V for LM2904AV-Q1/LM2904V-Q1.

7.7 Typical Characteristics

Typical characteristics section is applicable for LM2904B-Q1. The typical characteristics data section was taken with T_A = 25°C, V_S = 36 V (±18 V), V_{CM} = V_S / 2, R_{LOAD} = 10 kΩ connected to V_S / 2 (unless otherwise noted).

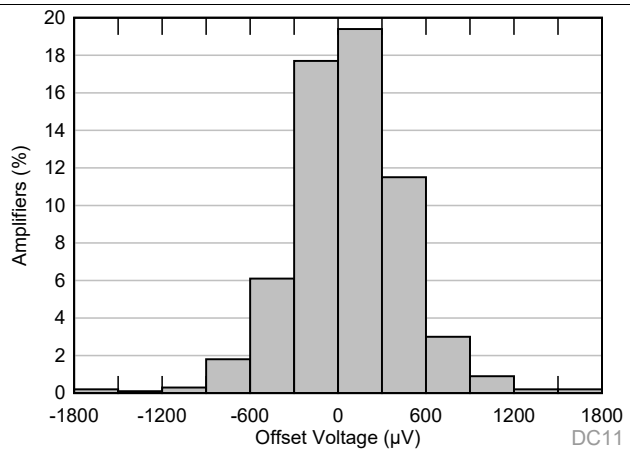


图 1. Offset Voltage Production Distribution

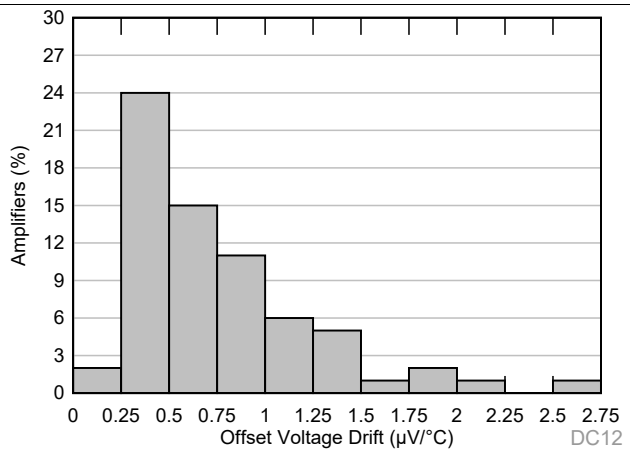


图 2. Offset Voltage Drift Distribution

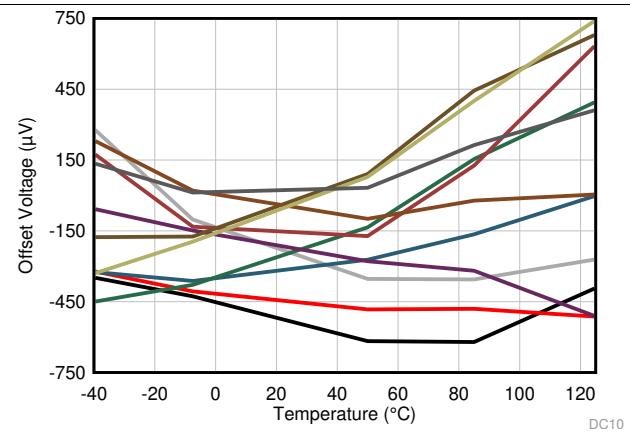


图 3. Offset Voltage vs Temperature

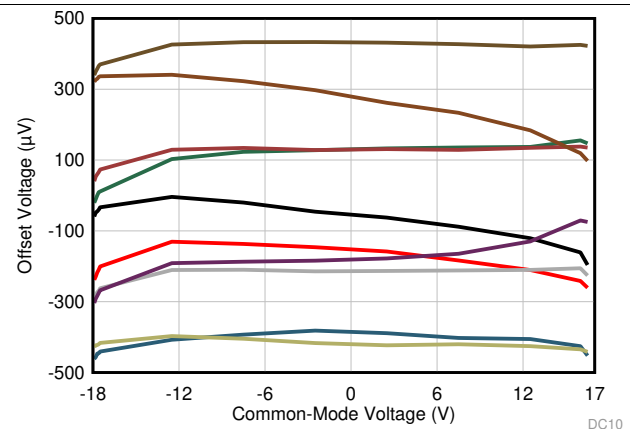


图 4. Offset Voltage vs Common-Mode Voltage

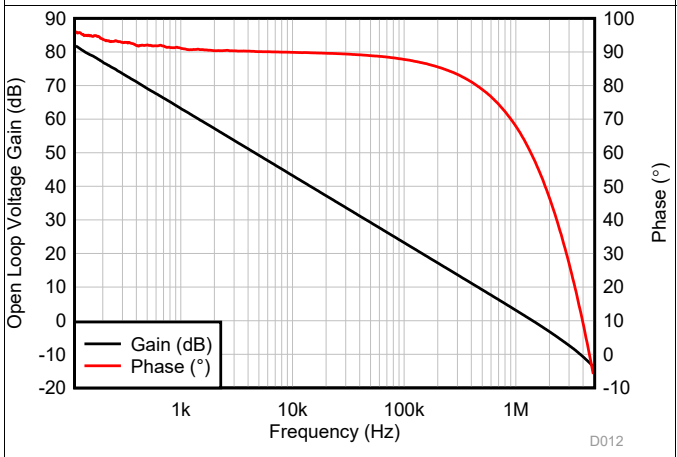


图 5. Open-Loop Gain and Phase vs Frequency

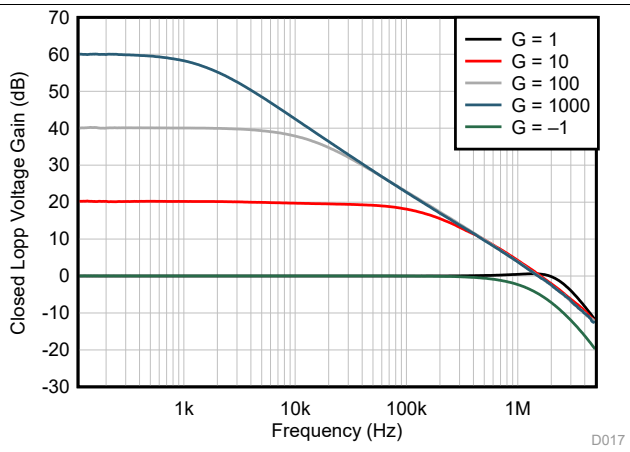


图 6. Closed-Loop Gain vs Frequency

Typical Characteristics (接下页)

Typical characteristics section is applicable for LM2904B-Q1. The typical characteristics data section was taken with T_A = 25°C, V_S = 36 V (±18 V), V_{CM} = V_S / 2, R_{LOAD} = 10 kΩ connected to V_S / 2 (unless otherwise noted).

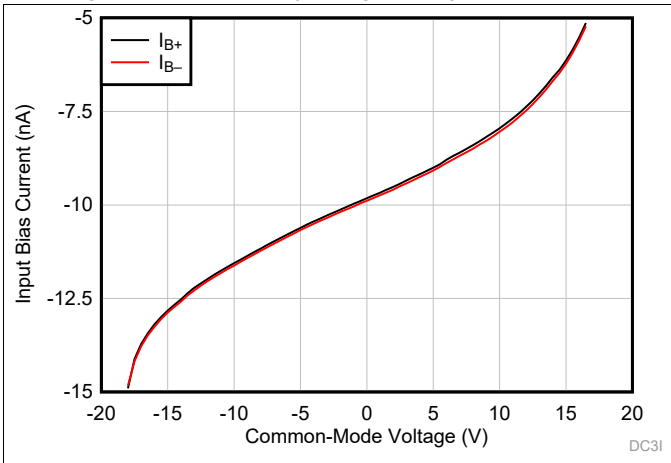


图 7. Input Bias Current vs Common-Mode Voltage

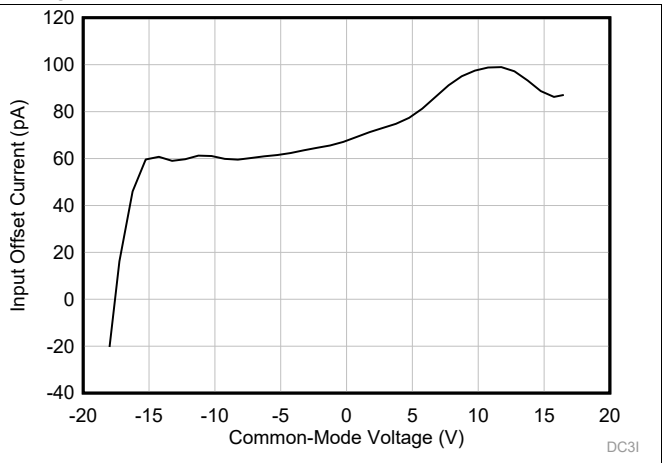


图 8. Input Offset Current vs Common-Mode Voltage

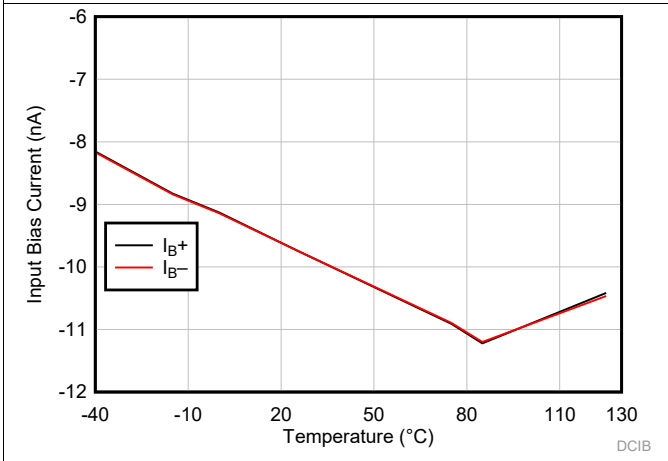


图 9. Input Bias Current vs Temperature

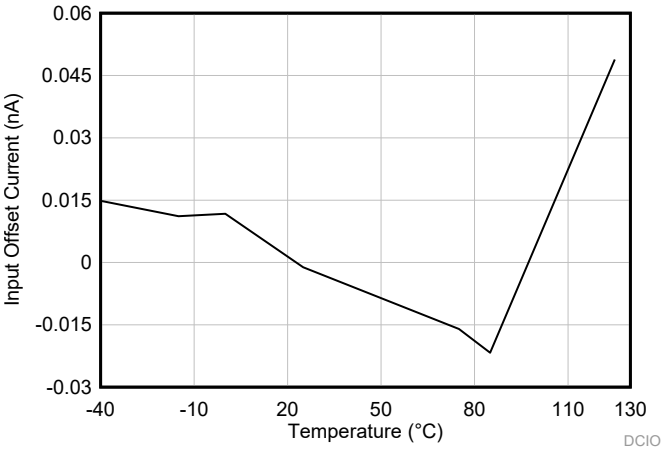


图 10. Input Offset Current vs Temperature

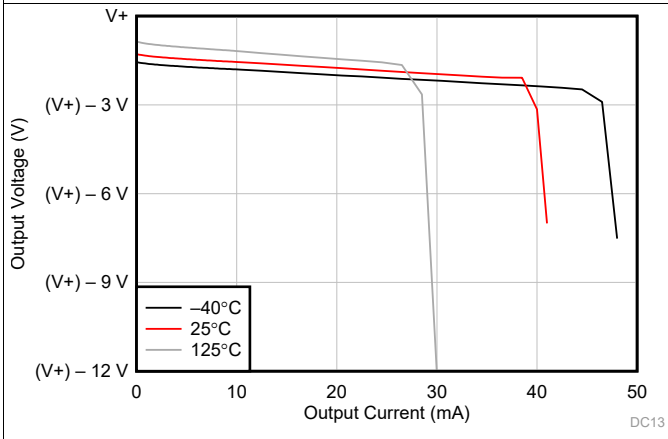


图 11. Output Voltage Swing vs Output Current (Sourcing)

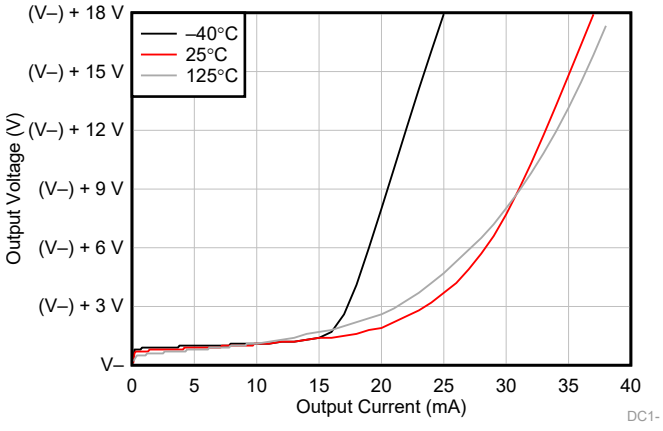


图 12. Output Voltage Swing vs Output Current (Sinking)

Typical Characteristics (接下页)

Typical characteristics section is applicable for LM2904B-Q1. The typical characteristics data section was taken with T_A = 25°C, V_S = 36 V (±18 V), V_{CM} = V_S / 2, R_{LOAD} = 10 kΩ connected to V_S / 2 (unless otherwise noted).

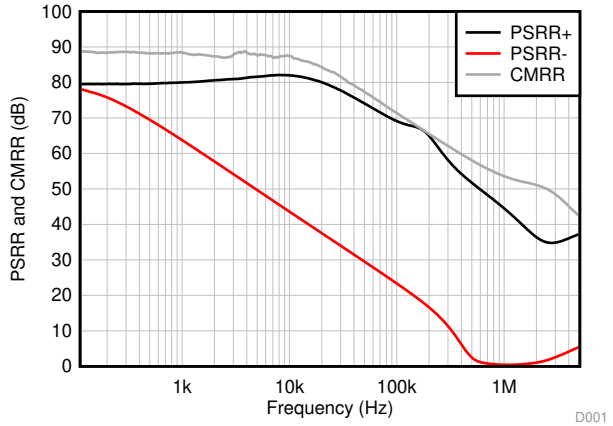


图 13. CMRR and PSRR vs Frequency

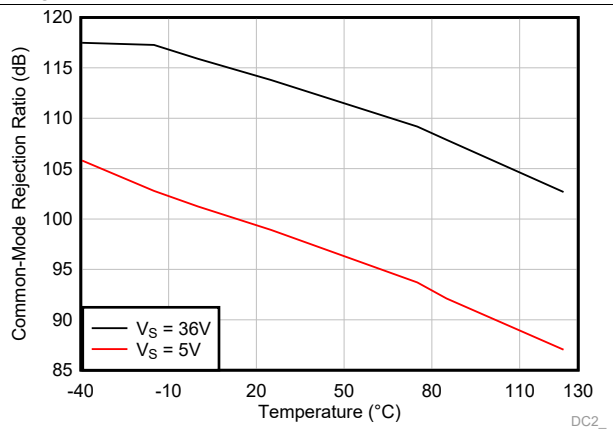
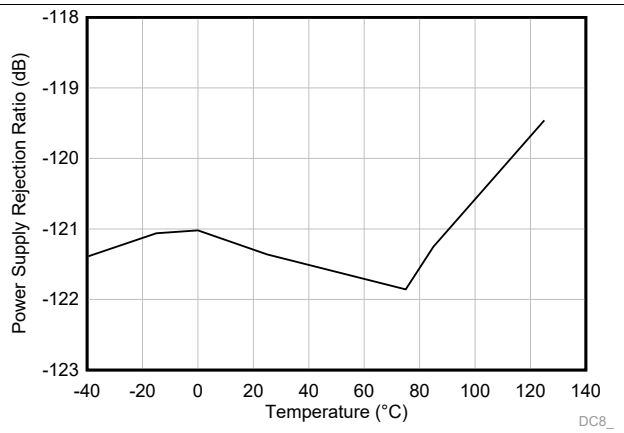


图 14. Common-Mode Rejection Ratio vs Temperature (dB)



V_S = 5 V to 36 V

图 15. Power Supply Rejection Ratio vs Temperature (dB)

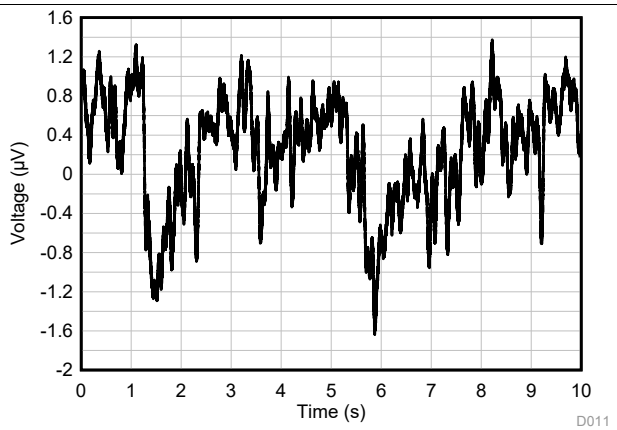


图 16. 0.1-Hz to 10-Hz Noise

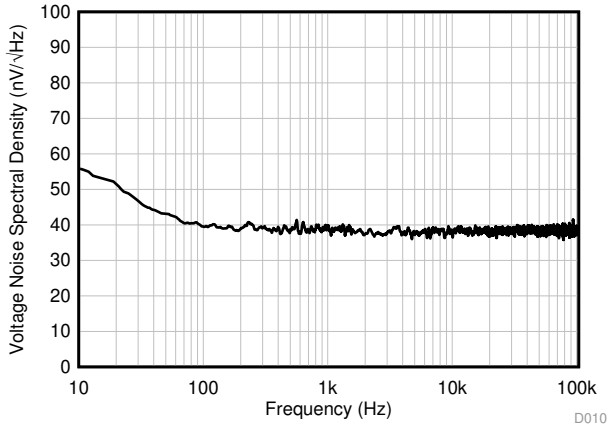
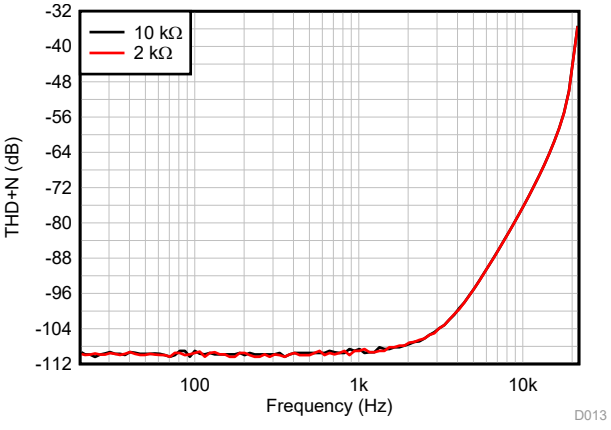


图 17. Input Voltage Noise Spectral Density vs Frequency

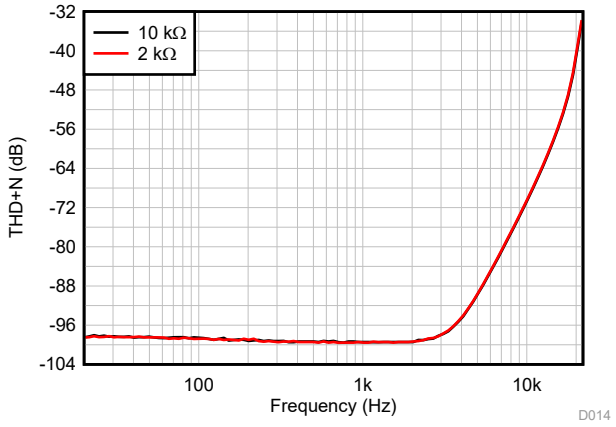


G = 1, f = 1 kHz, BW = 80 kHz,
V_{OUT} = 10 V_{PP}, R_L connected to V–

图 18. THD+N Ratio vs Frequency, G = 1

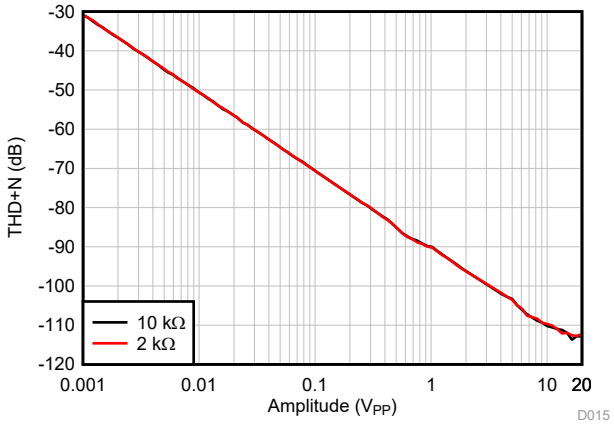
Typical Characteristics (接下页)

Typical characteristics section is applicable for LM2904B-Q1. The typical characteristics data section was taken with T_A = 25°C, V_S = 36 V (±18 V), V_{CM} = V_S / 2, R_{LOAD} = 10 kΩ connected to V_S / 2 (unless otherwise noted).



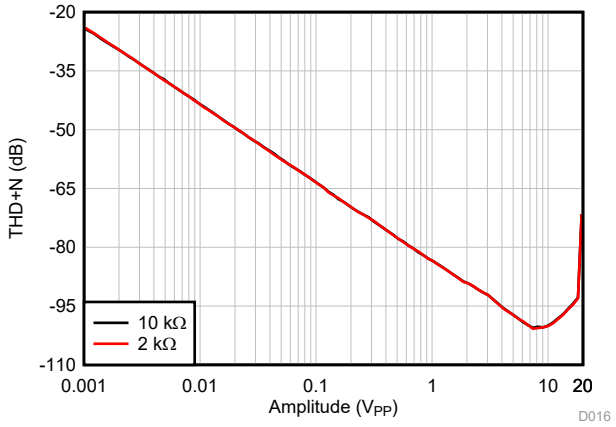
G = –1, f = 1 kHz, BW = 80 kHz,
V_{OUT} = 10 V_{PP}, R_L connected to V–

图 19. THD+N Ratio vs Frequency, G = –1



G = 1, f = 1 kHz, BW = 80 kHz,
R_L connected to V–

图 20. THD+N vs Output Amplitude, G = 1



G = –1, f = 1 kHz, BW = 80 kHz,
R_L connected to V–

图 21. THD+N vs Output Amplitude, G = –1

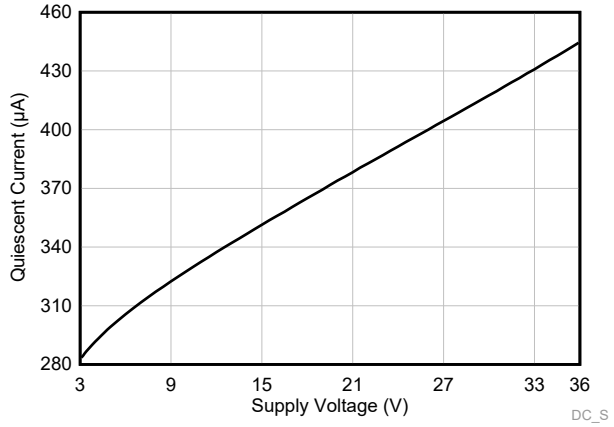


图 22. Quiescent Current vs Supply Voltage

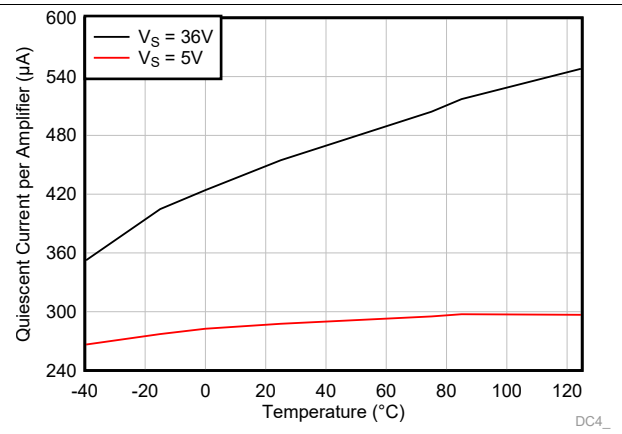


图 23. Quiescent Current vs Temperature

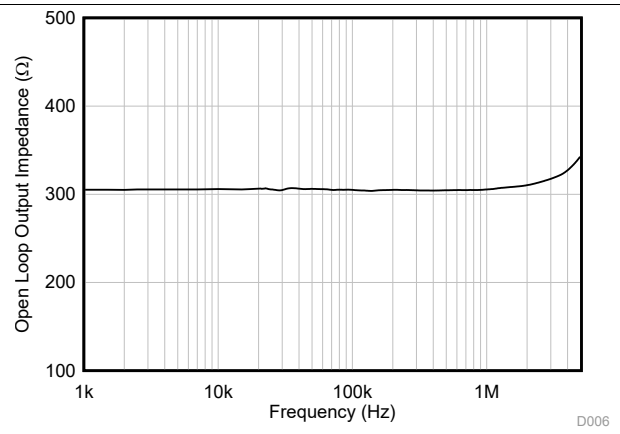
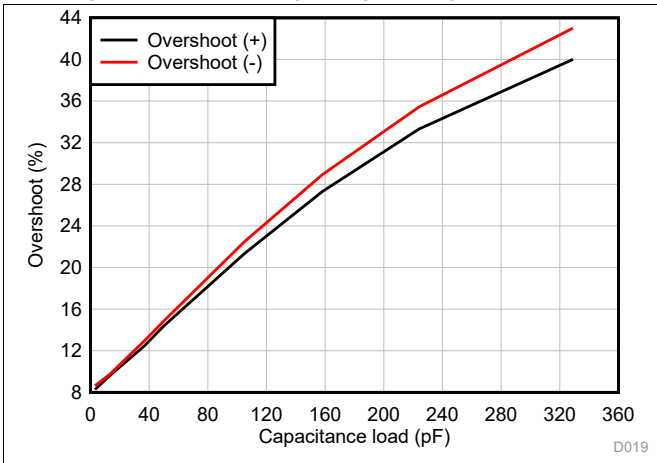


图 24. Open-Loop Output Impedance vs Frequency

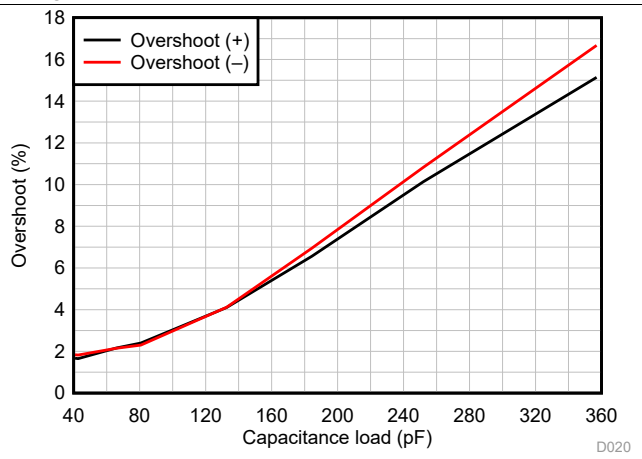
Typical Characteristics (接下页)

Typical characteristics section is applicable for LM2904B-Q1. The typical characteristics data section was taken with T_A = 25°C, V_S = 36 V (±18 V), V_{CM} = V_S / 2, R_{LOAD} = 10 kΩ connected to V_S / 2 (unless otherwise noted).



G = 1, 100-mV output step, R_L = open

图 25. Small-Signal Overshoot vs Capacitive Load



G = –1, 100-mV output step, R_L = open

图 26. Small-Signal Overshoot vs Capacitive Load

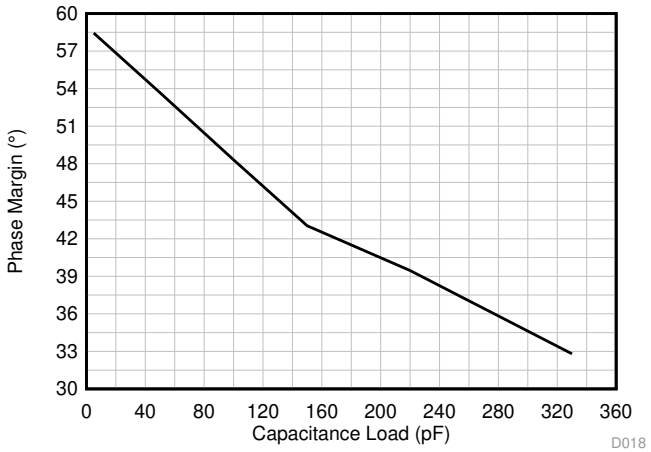
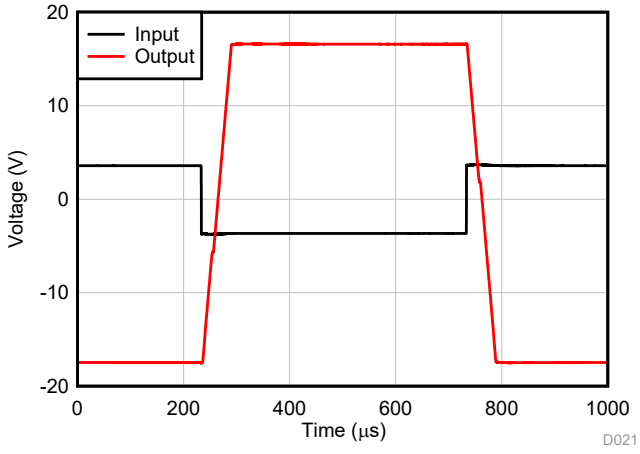
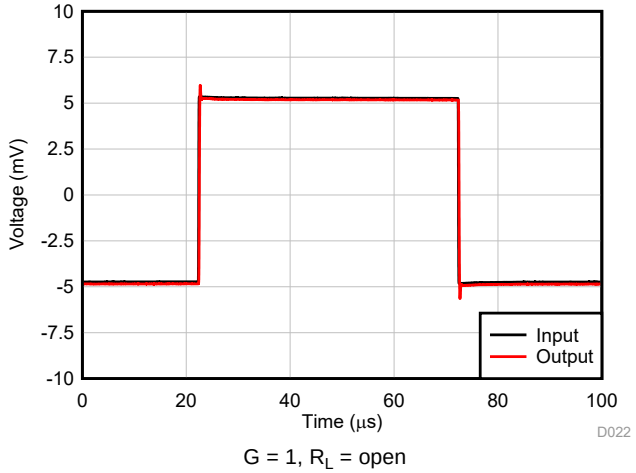


图 27. Phase Margin vs Capacitive Load



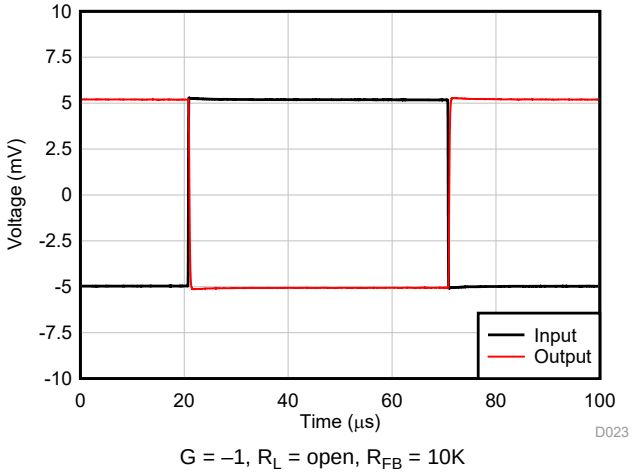
G = –10

图 28. Overload Recovery



G = 1, R_L = open

图 29. Small-Signal Step Response, G = 1

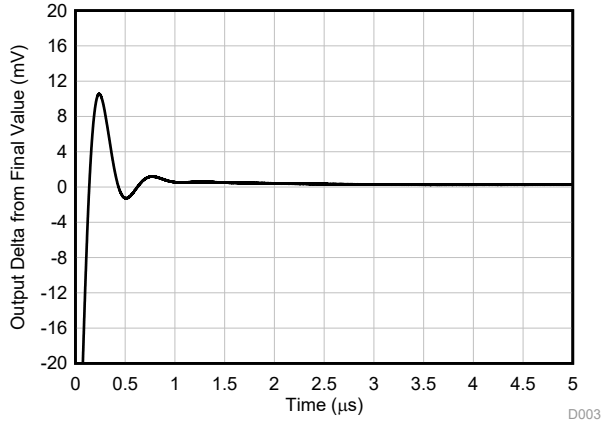


G = –1, R_L = open, R_{FB} = 10K

图 30. Small-Signal Step Response, G = –1

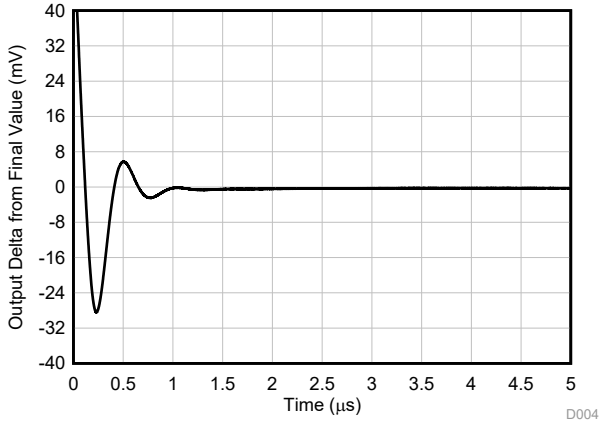
Typical Characteristics (接下页)

Typical characteristics section is applicable for LM2904B-Q1. The typical characteristics data section was taken with T_A = 25°C, V_S = 36 V (±18 V), V_{CM} = V_S / 2, R_{LOAD} = 10 kΩ connected to V_S / 2 (unless otherwise noted).



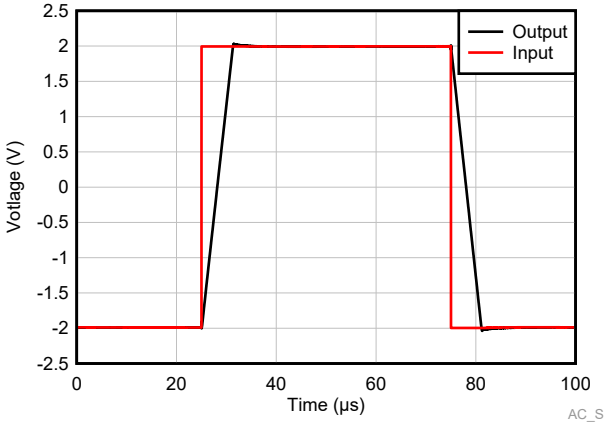
G = 1, R_L = open

图 31. Large-Signal Step Response (Rising)



G = 1, R_L = open

图 32. Large-Signal Step Response (Falling)



G = 1, R_L = open

图 33. Large-Signal Step Response

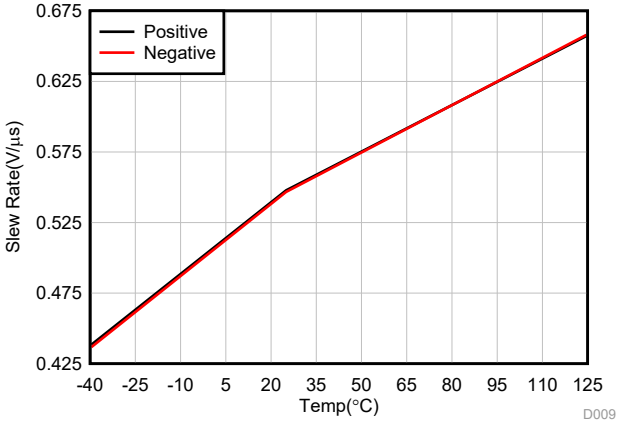


图 34. Slew Rate vs Temperature

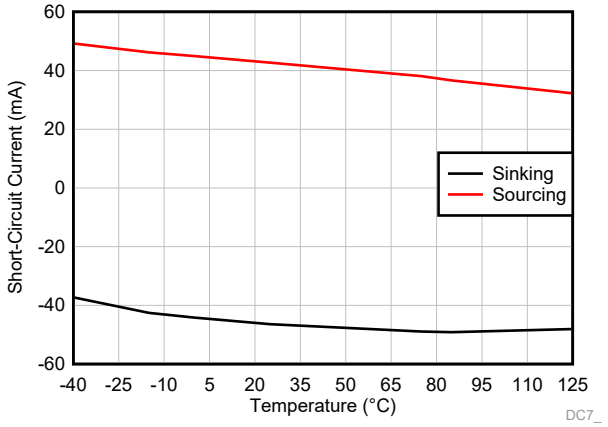
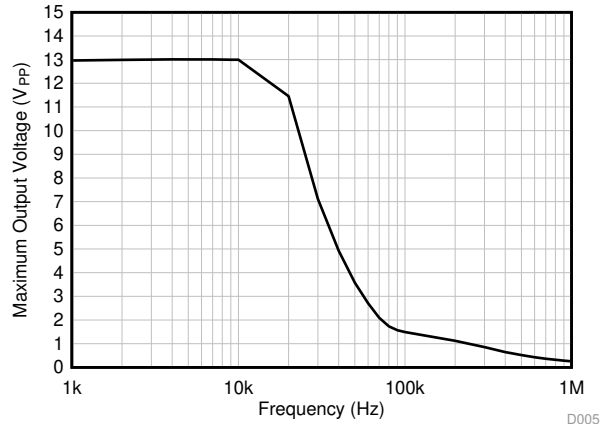


图 35. Short-Circuit Current vs Temperature



V_S = 15 V

图 36. Maximum Output Voltage vs Frequency

Typical Characteristics (接下页)

Typical characteristics section is applicable for LM2904B-Q1. The typical characteristics data section was taken with T_A = 25°C, V_S = 36 V (±18 V), V_{CM} = V_S / 2, R_{LOAD} = 10 kΩ connected to V_S / 2 (unless otherwise noted).

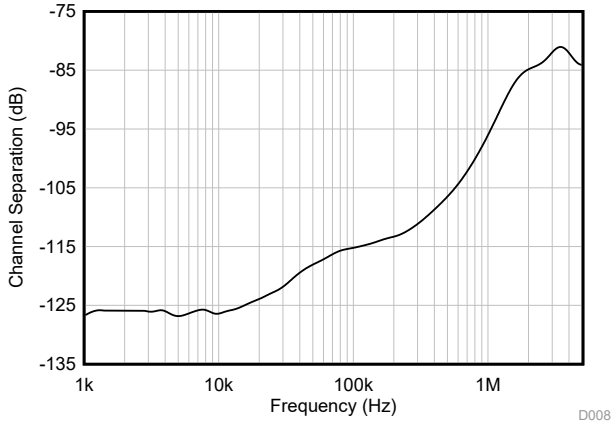


图 37. Channel Separation vs Frequency

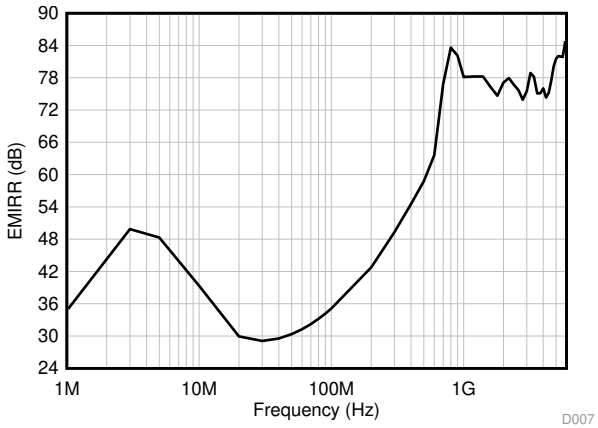


图 38. EMIRR (Electromagnetic Interference Rejection Ratio) vs Frequency

8 Parameter Measurement Information

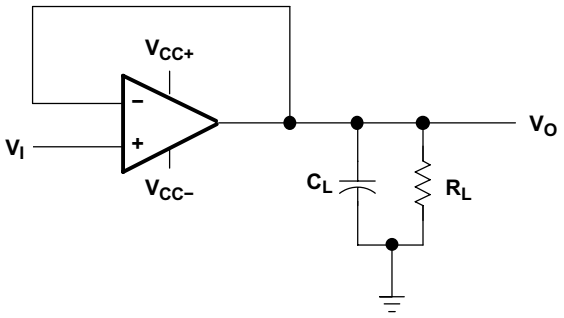


图 39. Unity-Gain Amplifier

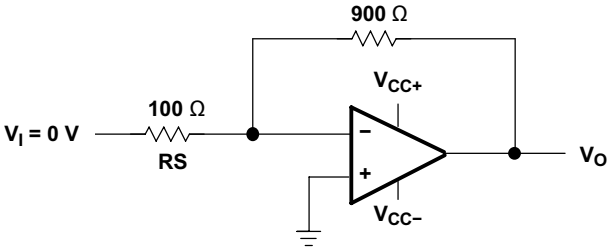


图 40. Noise-Test Circuit

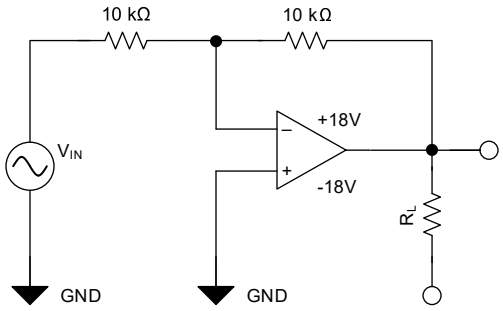


图 41. Test Circuit, G = –1, for THD+N and Small-Signal Step Response

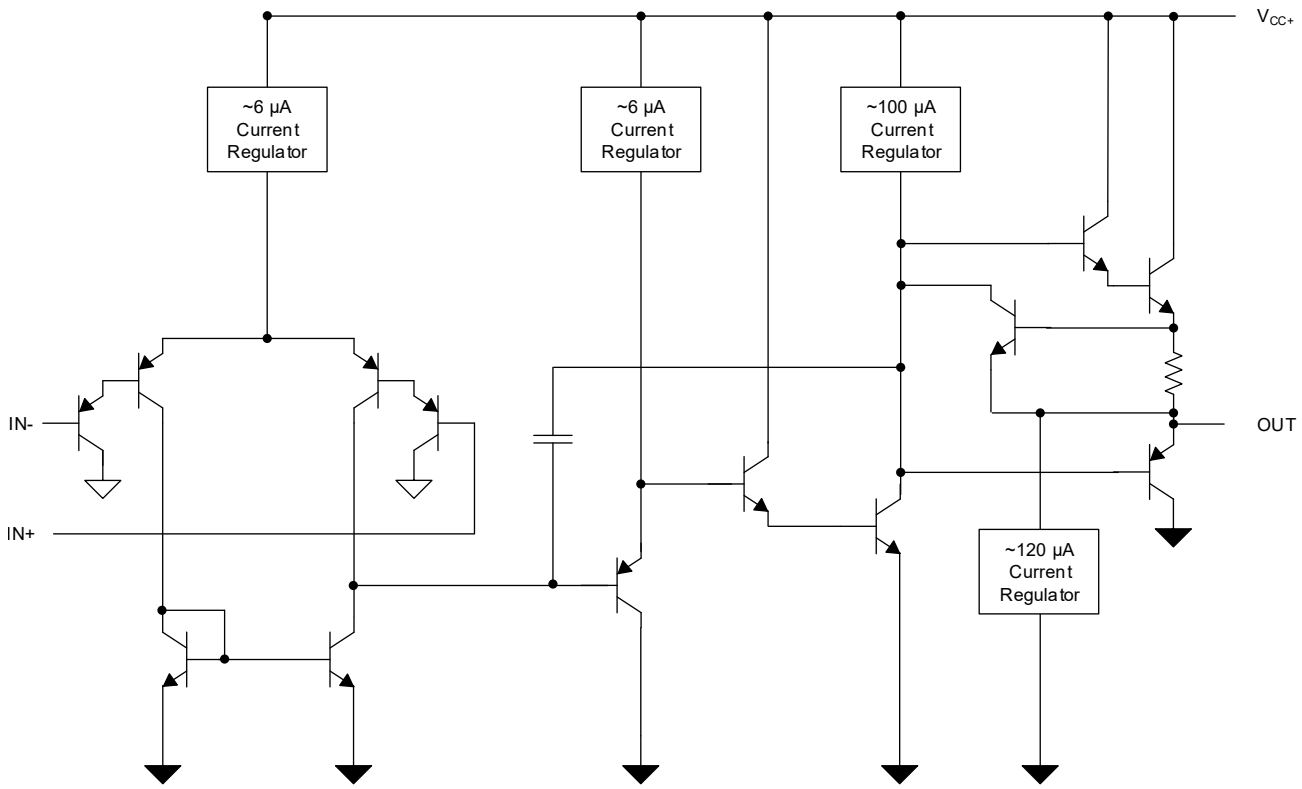
9 Detailed Description

9.1 Overview

The LM2904-Q1 and LM2904B-Q1 devices consist of two independent, high-gain frequency-compensated operational amplifiers designed to operate from a single supply over a wide range of voltages. Operation from split supplies also is possible if the difference between the two supplies is within the supply voltage range specified in the *Recommended Operating Conditions* section, and V_S is at least 1.5 V more positive than the input common-mode voltage. The low supply-current drain is independent of the magnitude of the supply voltage.

Applications include transducer amplifiers, dc amplification blocks, and all the conventional operational amplifier circuits that now can be implemented more easily in single-supply-voltage systems. For example, these devices can be operated directly from the standard 5-V supply used in digital systems and easily can provide the required interface electronics without additional ±5-V supplies.

9.2 Functional Block Diagram



9.3 Feature Description

9.3.1 Unity-Gain Bandwidth

The unity-gain bandwidth is the frequency up to which an amplifier with a unity gain may be operated without greatly distorting the signal. These devices have a 1.2-MHz unity-gain bandwidth (LM2904B-Q1).

9.3.2 Slew Rate

The slew rate is the rate at which an operational amplifier can change its output when there is a change on the input. These devices have a 0.5-V/µs slew rate (LM2904B-Q1).

9.3.3 Input Common Mode Range

The valid common mode range is from device ground to V_S – 1.5 V (V_S – 2 V across temperature). Inputs may exceed V_S up to the maximum V_S without device damage. At least one input must be in the valid input common-mode range for the output to be the correct phase. If both inputs exceed the valid range, then the output phase is undefined. If either input more than 0.3 V below V– then input current should be limited to 1 mA and the output phase is undefined.

9.4 Device Functional Modes

The LM2904-Q1 and LM2904B-Q1 devices are powered on when the supply is connected. This device can be operated as a single-supply operational amplifier or dual-supply amplifier, depending on the application.

10 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

10.1 Application Information

The LM2904-Q1 and LM2904B-Q1 operational amplifiers are useful in a wide range of signal conditioning applications. Inputs can be powered before V_S for flexibility in multiple supply circuits. For full application design guidelines related to this family of devices, please refer to the application report *Application design guidelines for LM324/LM358 devices*.

10.2 Typical Application

A typical application for an operational amplifier is an inverting amplifier. This amplifier takes a positive voltage on the input, and makes it a negative voltage of the same magnitude. In the same manner, it also makes negative voltages positive.

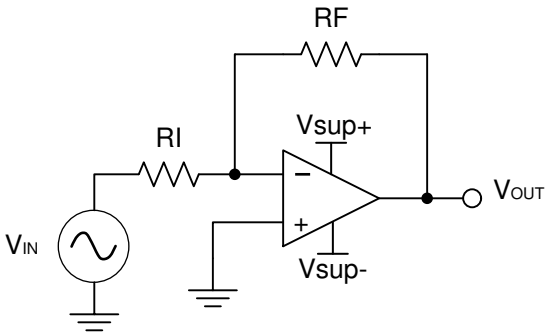


图 42. Application Schematic

10.2.1 Design Requirements

The supply voltage must be chosen such that it is larger than the input voltage range and output range. For instance, this application scales a signal of ±0.5 V to ±1.8 V. Setting the supply at ±12 V is sufficient to accommodate this application.

10.2.2 Detailed Design Procedure

Determine the gain required by the inverting amplifier using 公式 1 and 公式 2:

$$A_V = \frac{VOUT}{VIN} \tag{1}$$

$$A_V = \frac{1.8}{-0.5} = -3.6 \tag{2}$$

Once the desired gain is determined, choose a value for R_I or R_F. Choosing a value in the kilohm range is desirable because the amplifier circuit uses currents in the milliampere range. This ensures the part does not draw too much current. This example uses 10 kΩ for R_I which means 36 kΩ is used for R_F. This was determined by 公式 3.

$$A_V = -\frac{RF}{RI} \tag{3}$$

Typical Application (接下页)

10.2.3 Application Curve

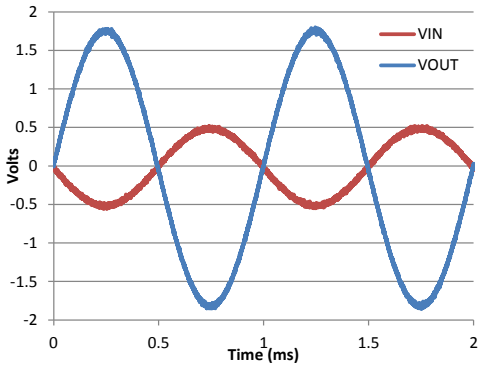


图 43. Input and Output Voltages of the Inverting Amplifier

11 Power Supply Recommendations

CAUTION

Supply voltages larger than specified in the recommended operating region can permanently damage the device (see the *Absolute Maximum Ratings*).

Place 0.1-µF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies. For more detailed information on bypass capacitor placement, see the *Layout* section.

12 Layout

12.1 Layout Guidelines

For best operational performance of the device, use good PCB layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole, as well as the operational amplifier. Bypass capacitors are used to reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
  - Connect low-ESR, 0.1-µF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for single-supply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most-effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces EMI noise pickup. Make sure to physically separate digital and analog grounds, paying attention to the flow of the ground current.
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If it is not possible to keep them separate, it is much better to cross the sensitive trace perpendicular as opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible. Keeping R_F and R_G close to the inverting input minimizes parasitic capacitance, as shown in the *Layout Examples* section.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.

12.2 Layout Examples

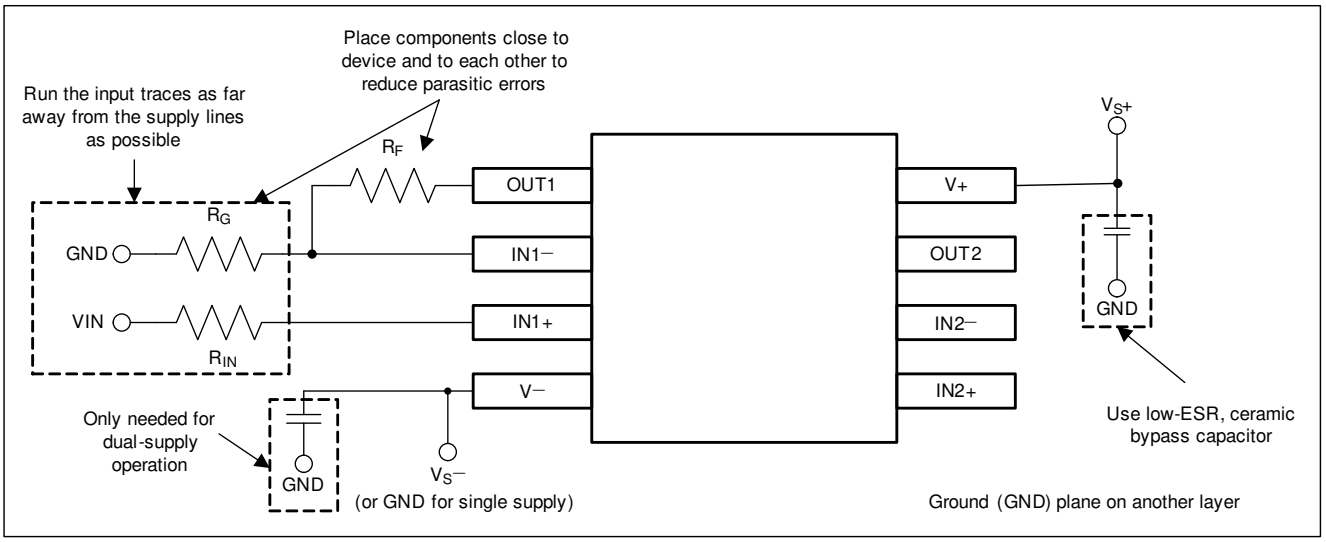


图 44. Operational Amplifier Board Layout for Noninverting Configuration

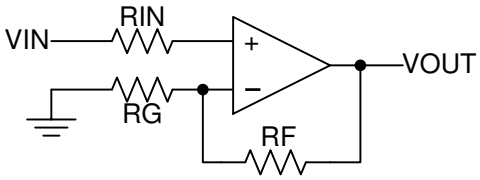


图 45. Operational Amplifier Schematic for Noninverting Configuration

13 器件和文档支持

13.1 文档支持

13.1.1 相关文档

请参阅如下相关文档：德州仪器 (TI)， *《LM324/LM358 器件应用设计指南》* 应用报告

13.2 相关链接

下表列出了快速访问链接。类别包括技术文档、支持和社区资源、工具和软件，以及立即订购快速访问。

表 **1.** 相关链接

器件	产品文件夹	立即订购	技术文档	工具与软件	支持和社区
LM2904-Q1	单击此处	单击此处	单击此处	单击此处	单击此处
LM2904B-Q1	单击此处	单击此处	单击此处	单击此处	单击此处

13.3 接收文档更新通知

要接收文档更新通知，请导航至 ti.com.cn 上的器件产品文件夹。单击右上角的*通知我*进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

13.4 社区资源

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

13.5 商标

E2E is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

13.6 静电放电警告

ESD 可能会损坏该集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理措施和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。 精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

13.7 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

14 机械、封装和可订购信息

以下页中包括机械、封装和可订购信息。这些信息是针对指定器件可提供的最新数据。数据如有变更，恕不另行通知和修订此文档。如需获取此数据表的浏览器版本，请查看左侧的导航面板。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LM2904AVQDRG4Q1	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2904AVQ	Samples
LM2904AVQDRQ1	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2904AVQ	Samples
LM2904AVQPWRG4Q1	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2904AVQ	Samples
LM2904AVQPWRQ1	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2904AVQ	Samples
LM2904BQDGKRQ1	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	27ZB	Samples
LM2904BQDRQ1	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	2904BQ	Samples
LM2904BQPWRQ1	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2904BQ	Samples
LM2904BTQDGKRQ1	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	4BTQ	Samples
LM2904QDRG4Q1	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2904Q1	Samples
LM2904QDRQ1	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2904Q1	Samples
LM2904QPWRG4Q1	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2904Q1	Samples
LM2904QPWRQ1	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2904Q1	Samples
LM2904VQDRG4Q1	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2904VQ	Samples
LM2904VQDRQ1	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2904VQ1	Samples
LM2904VQPWRG4Q1	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2904VQ	Samples
LM2904VQPWRQ1	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2904VQ	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

OTHER QUALIFIED VERSIONS OF LM2904-Q1, LM2904B-Q1 :

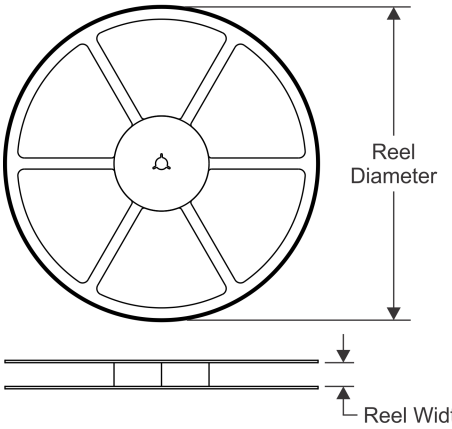
- Catalog : LM2904, LM2904B
- Enhanced Product : LM2904-EP

NOTE: Qualified Version Definitions:

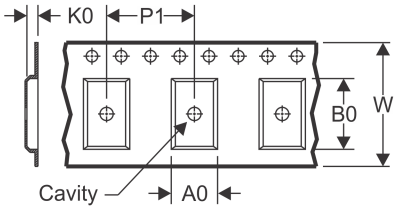
- Catalog - TI's standard catalog product
- Enhanced Product - Supports Defense, Aerospace and Medical Applications

TAPE AND REEL INFORMATION

REEL DIMENSIONS

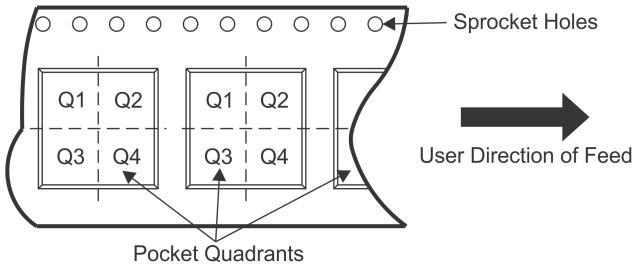


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

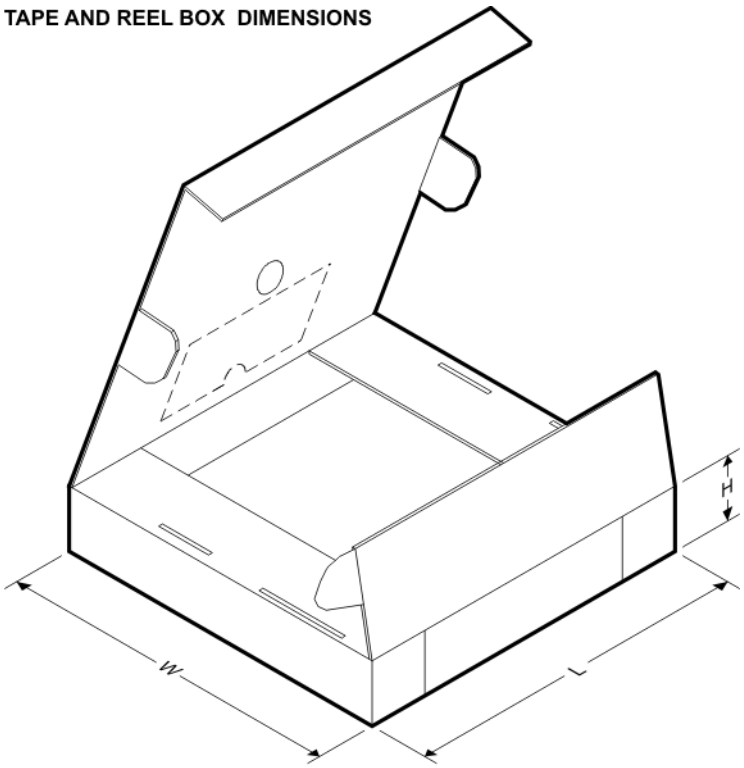
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

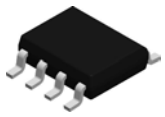
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LM2904AVQDRG4Q1	SOIC	D	8	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
LM2904AVQDRQ1	SOIC	D	8	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
LM2904AVQPWRG4Q1	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LM2904AVQPWRQ1	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LM2904BQDGKRQ1	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LM2904BQDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LM2904BQPWRQ1	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LM2904BTQDGKRQ1	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LM2904QDRG4Q1	SOIC	D	8	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
LM2904QDRQ1	SOIC	D	8	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
LM2904QPWRG4Q1	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LM2904QPWRQ1	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LM2904VQDRG4Q1	SOIC	D	8	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
LM2904VQDRQ1	SOIC	D	8	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
LM2904VQPWRG4Q1	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LM2904VQPWRQ1	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LM2904AVQDRG4Q1	SOIC	D	8	2500	340.5	338.1	20.6
LM2904AVQDRQ1	SOIC	D	8	2500	340.5	338.1	20.6
LM2904AVQPWRG4Q1	TSSOP	PW	8	2000	367.0	367.0	35.0
LM2904AVQPWRQ1	TSSOP	PW	8	2000	853.0	449.0	35.0
LM2904BQDGKRQ1	VSSOP	DGK	8	2500	366.0	364.0	50.0
LM2904BQDRQ1	SOIC	D	8	2500	340.5	338.1	20.6
LM2904BQPWRQ1	TSSOP	PW	8	2000	853.0	449.0	35.0
LM2904BTQDGKRQ1	VSSOP	DGK	8	2500	366.0	364.0	50.0
LM2904QDRG4Q1	SOIC	D	8	2500	340.5	338.1	20.6
LM2904QDRQ1	SOIC	D	8	2500	340.5	338.1	20.6
LM2904QPWRG4Q1	TSSOP	PW	8	2000	853.0	449.0	35.0
LM2904QPWRQ1	TSSOP	PW	8	2000	853.0	449.0	35.0
LM2904VQDRG4Q1	SOIC	D	8	2500	340.5	338.1	20.6
LM2904VQDRQ1	SOIC	D	8	2500	340.5	338.1	20.6
LM2904VQPWRG4Q1	TSSOP	PW	8	2000	367.0	367.0	35.0
LM2904VQPWRQ1	TSSOP	PW	8	2000	853.0	449.0	35.0

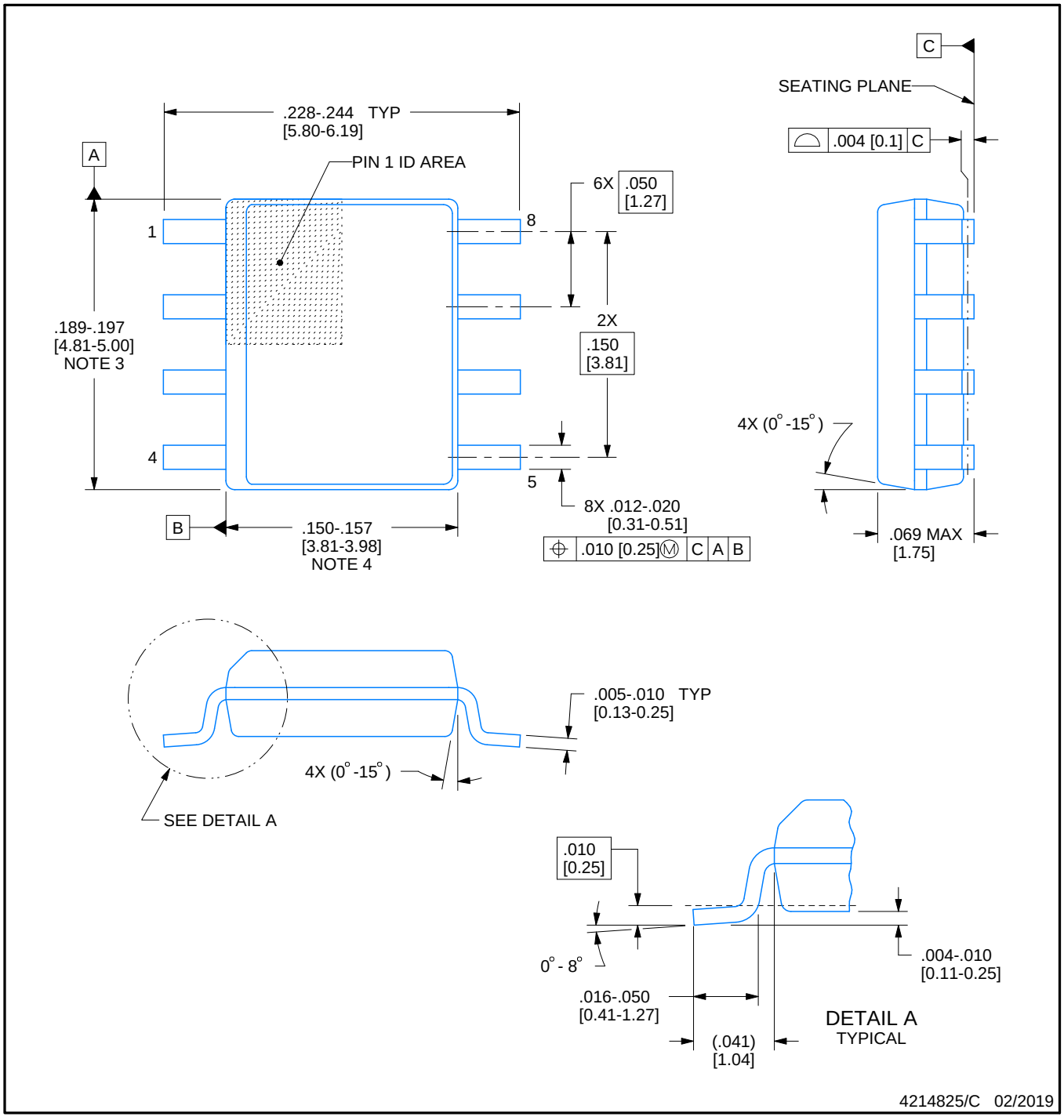


PACKAGE OUTLINE

D0008A

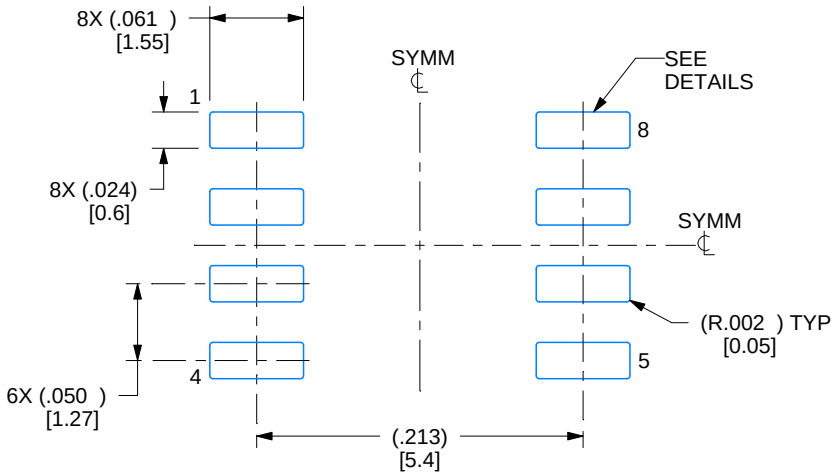
SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT

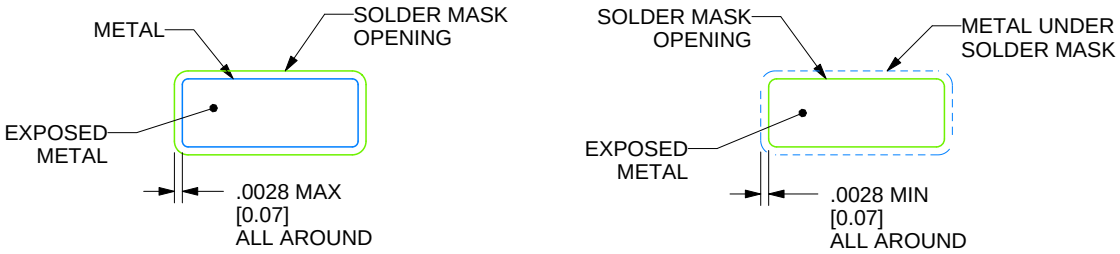


NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

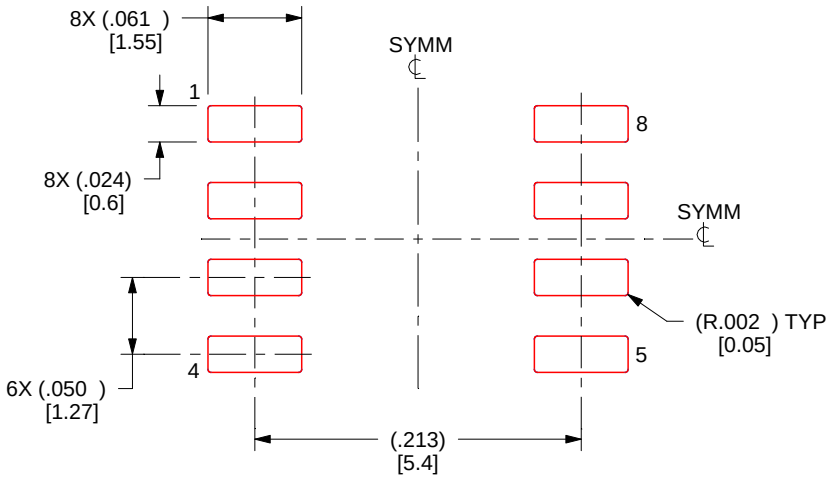
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



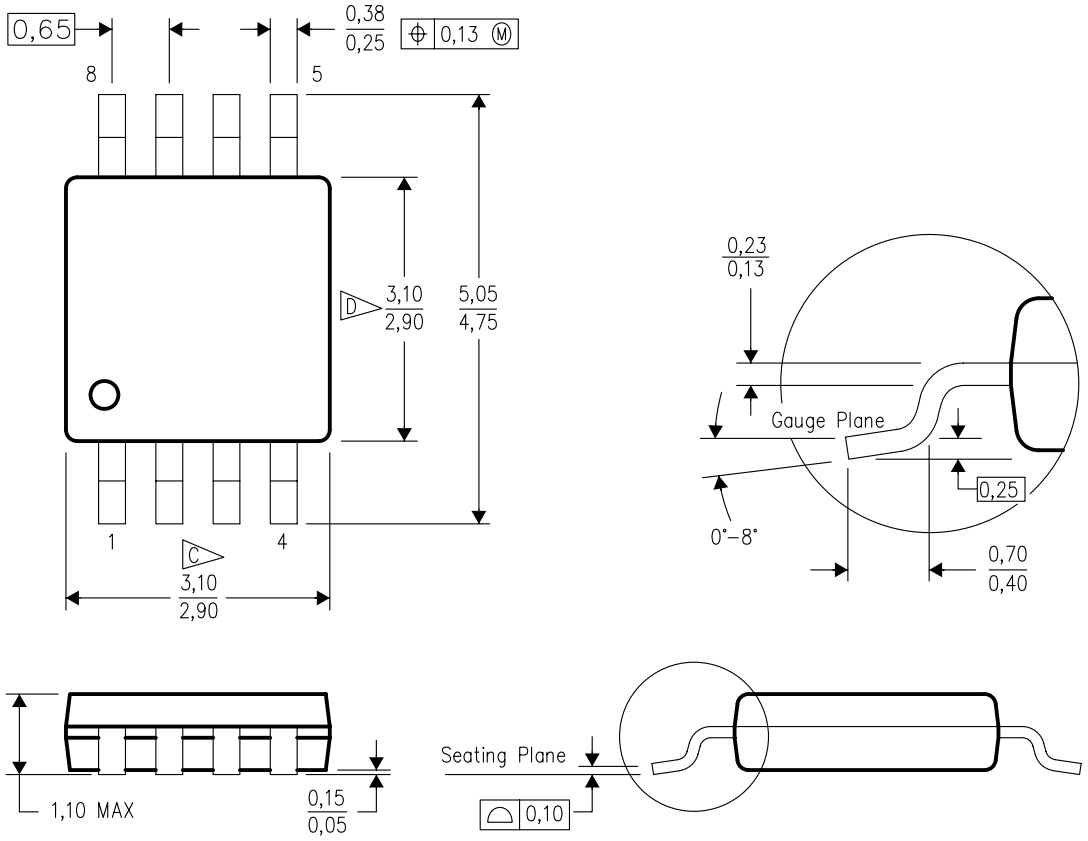
SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

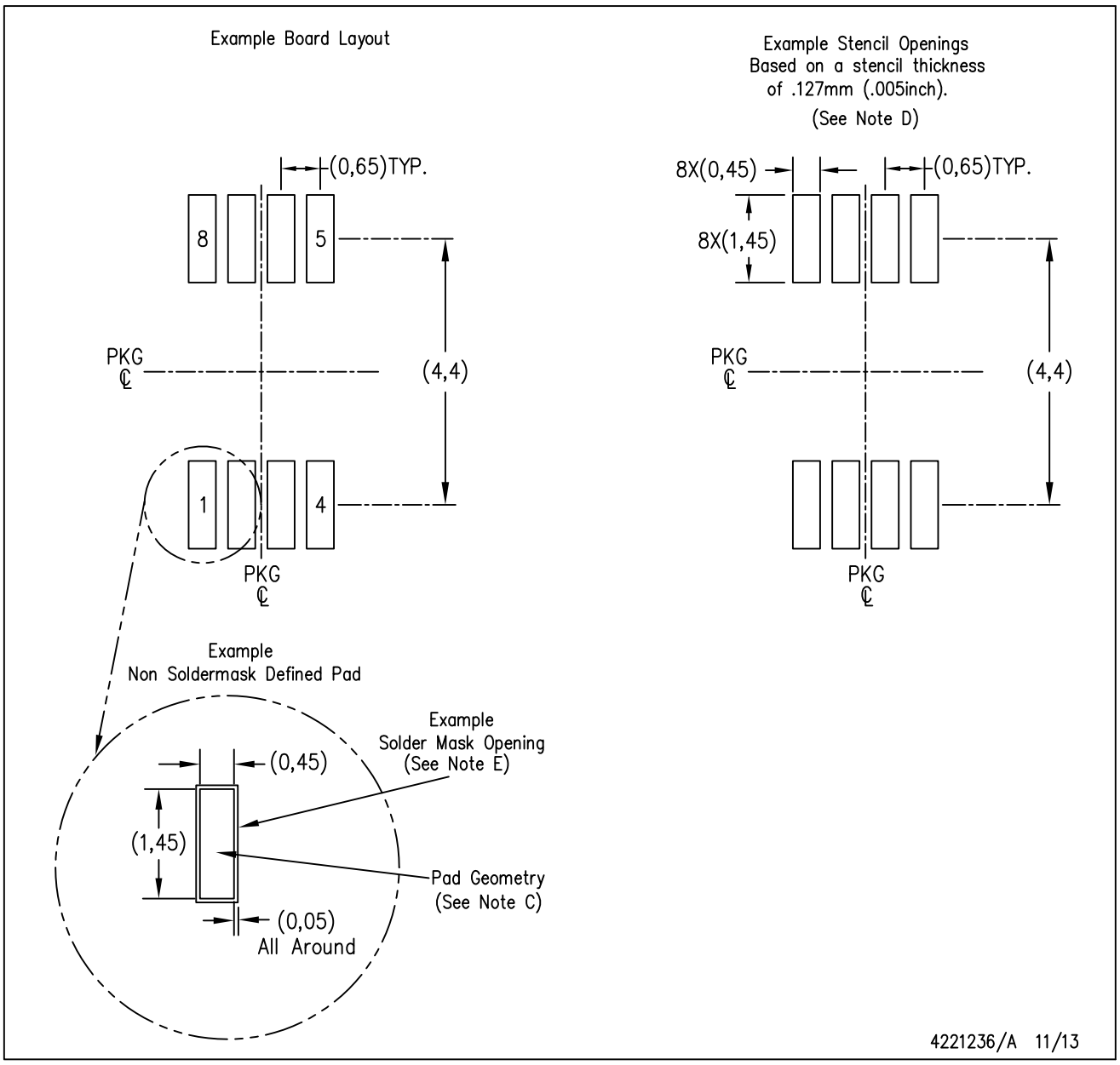
DGK (S–PDSO–G8) PLASTIC SMALL–OUTLINE PACKAGE



4073329/E 05/06

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per end.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
E. Falls within JEDEC MO–187 variation AA, except interlead flash.

DGK (S–PDSO–G8) PLASTIC SMALL OUTLINE PACKAGE



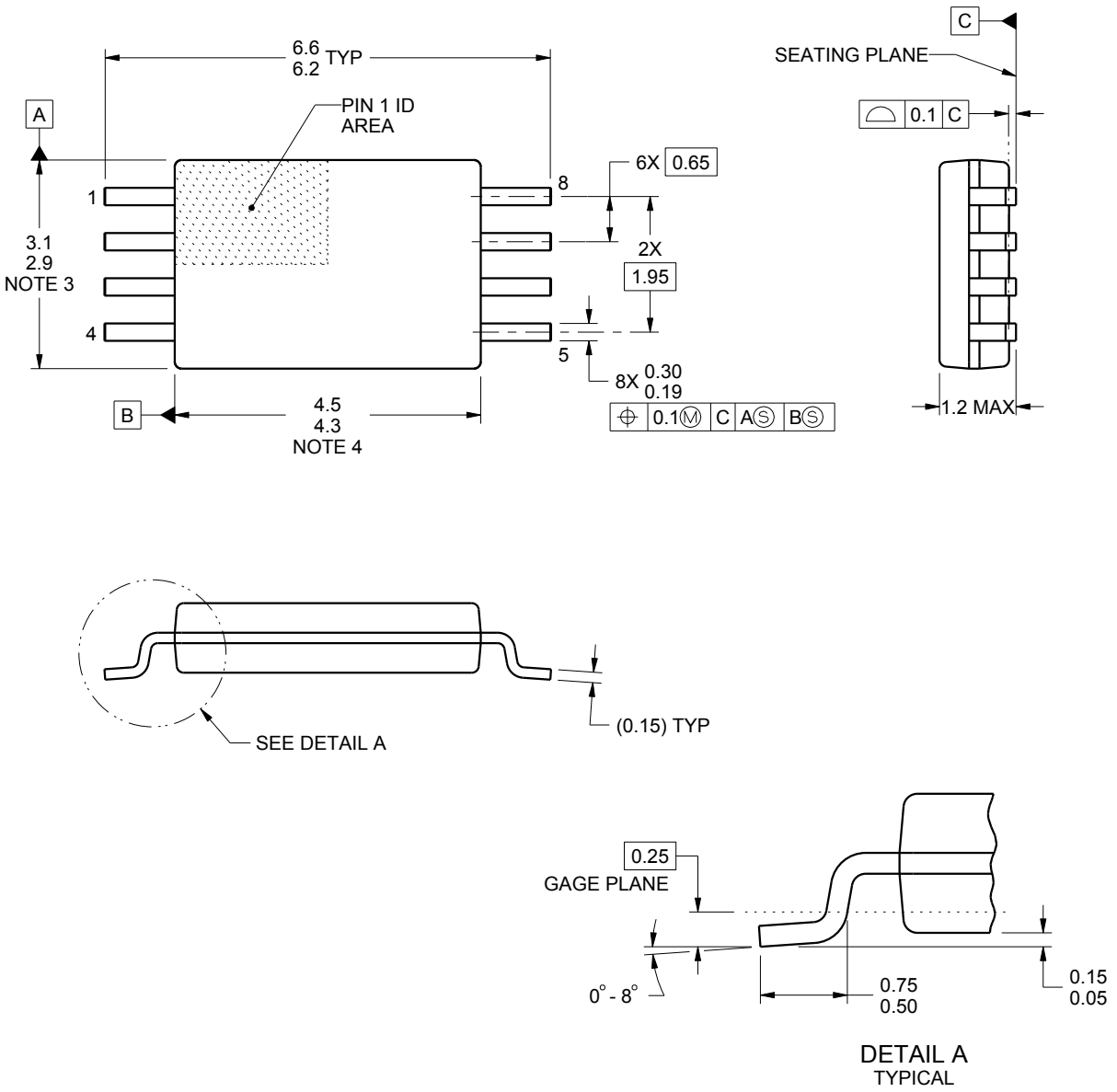
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

PACKAGE OUTLINE

PW0008A

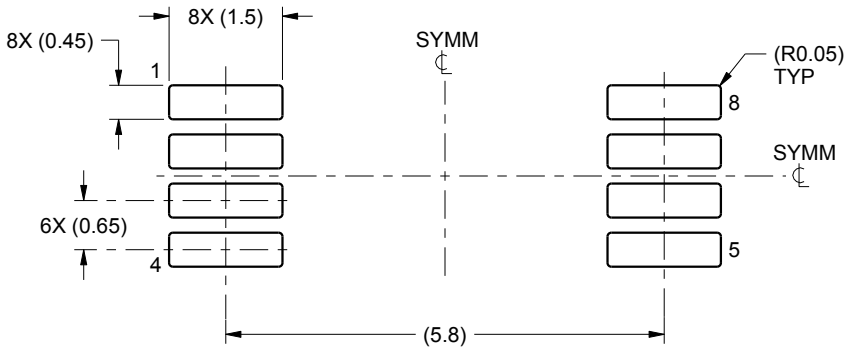
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE

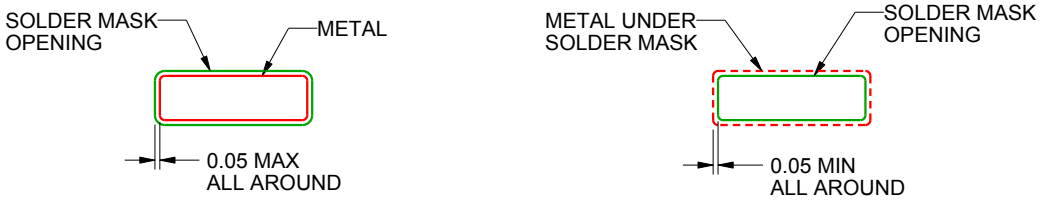


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153, variation AA.



LAND PATTERN EXAMPLE
SCALE:10X

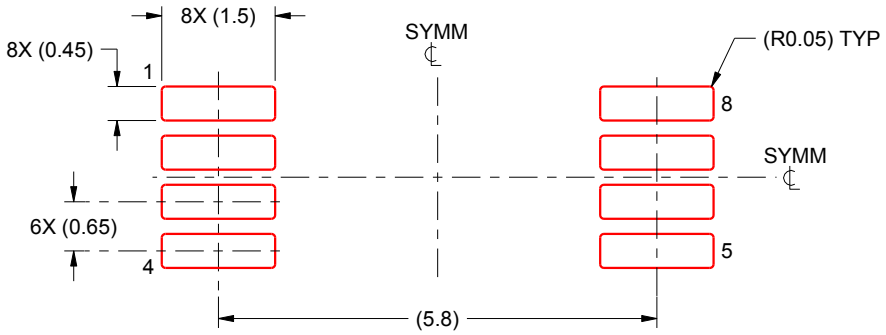


SOLDER MASK DETAILS
NOT TO SCALE

4221848/A 02/2015

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:10X

4221848/A 02/2015

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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